

# **EXS210067-03**

**EXS0790-020-10-0B00030**

**790nm UNCOOLED TO-56**

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**Confidentiality:** **None**

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## 1. SCOPE

### 1.1 PURPOSE

The purpose of this document is to specify the electro-optical performance and dimensions of superluminescent light emitting diode (SLED) TO-56.

### 1.2 RESPONSIBILITY

EXALOS is responsible for establishing, implementing and maintaining this procedure. The Quality representative shall ensure that a timely Engineering Change Notice (ECN) is issued in accordance with EXALOS procedure for any changes.

## 2. REFERENCE DOCUMENT

- EXS-WI-0001 Visual Inspection Criteria SLED Chip on Submount Procedure
- MIL STD 883 C method.
- Bellcore GR-468-CORE

## 3. ELECTRO-OPTICAL PERFORMANCE ( $T_{SLED} = 25^{\circ}C$ )

Parameter	Symbol	Cond.	Min	Typ	Max	Unit
Operating Current	$I_{op}$				120	mA
Power ex-window	$P_o$	$I_{op, max}$	9	15		mW
Centre Wavelength*	$\lambda_c$	$I_{op, max}$	770	790	810	nm
Bandwidth FWHM*		$I_{op, max}$	16	20		nm
Spectral ripple [RB=0.1 nm]		$I_{op, max}$	-	0.1	-	dB
Monitor Diode Current <sup>†</sup>	$I_{MPD}$	$I_{op, max}$	50			$\mu A$
Monitor diode bias voltage	$V_{Bias}$		0		-12	V
Vertical Far Field Angle		$I_{op, max}$	35	40	45	degrees
Horizontal Far Field Angle		$I_{op, max}$	10	13	16	degrees

\*Spectral verification is performed by sampling at the manufacturing batch level. Manufacturing batches are defined by epitaxial wafer growth run

<sup>†</sup> Measurement conditions:

- $I_{op} = I_{op} \text{ Max}$
  - Monitor PD bias voltage: 0 Volts
- Input resistance of the Monitor PD current measurement circuit 10 Ohm

#### 4. ABSOLUTE MAXIMUM RATINGS

Stresses beyond the absolute maximum ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Parameter	Symbol	Cond.	Min	Max	Unit
Forward current	$I_F$	$P_o \leq P_{max}$		130	mA
Reverse voltage	$V_R$			-2	V
Forward voltage	$V_F$	$I_{F,max}$		3.0	V
Storage temperature	$T_{stg}$		-40	85	°C
Operating temperature	$T_{op}$	$I_{F,max}$	-20	70	°C
Max Power ex-window <sup>‡</sup>	$P_{max}$			25	mW
Lead soldering temperature				260	°C
ESD		human b.m		500	V

#### 5. SCREENING (EXS210067-03)

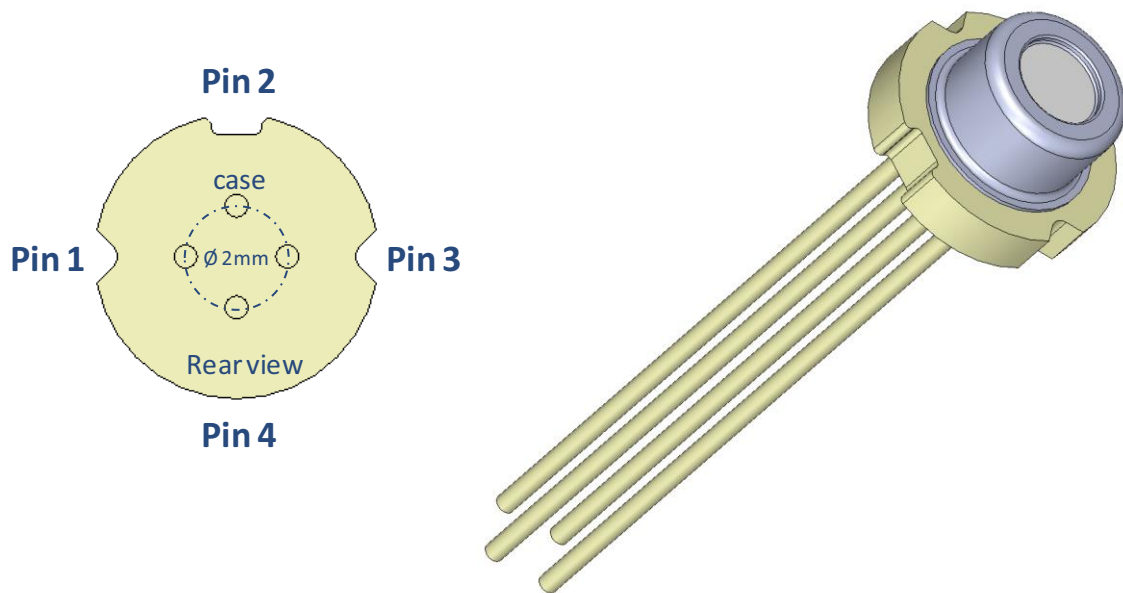
The manufactured 790nm SLED Module is required to meet all operating conditions specified in Table 3.1, Electro-Optical Performance Specifications after being subjected to the following screening tests.

Test Item	Test Conditions	Reference	Sample
Hermetic Seal	Fine leak :	MIL-STD-883, Method 1014	100 %
	Max. leak rate $5 \times 10^{-8}$ atm.cc/sec	Condition A	
Temperature Cycling	Gross leak :	MIL-STD-883, Method 1014	100 %
	-40°C to +85°C, ramp rate $\geq 5^\circ\text{C}/\text{min}$ 20 cycles	Condition C	
		MIL-STD-883, Method 1010	100%

<sup>‡</sup> The drive current may need to be adjusted in order not to exceed the maximum power rating for low ambient temperature.

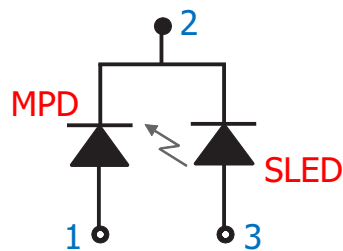
6. PACKAGE DIMENSIONS [mm]

Tolerances: See section 6.2



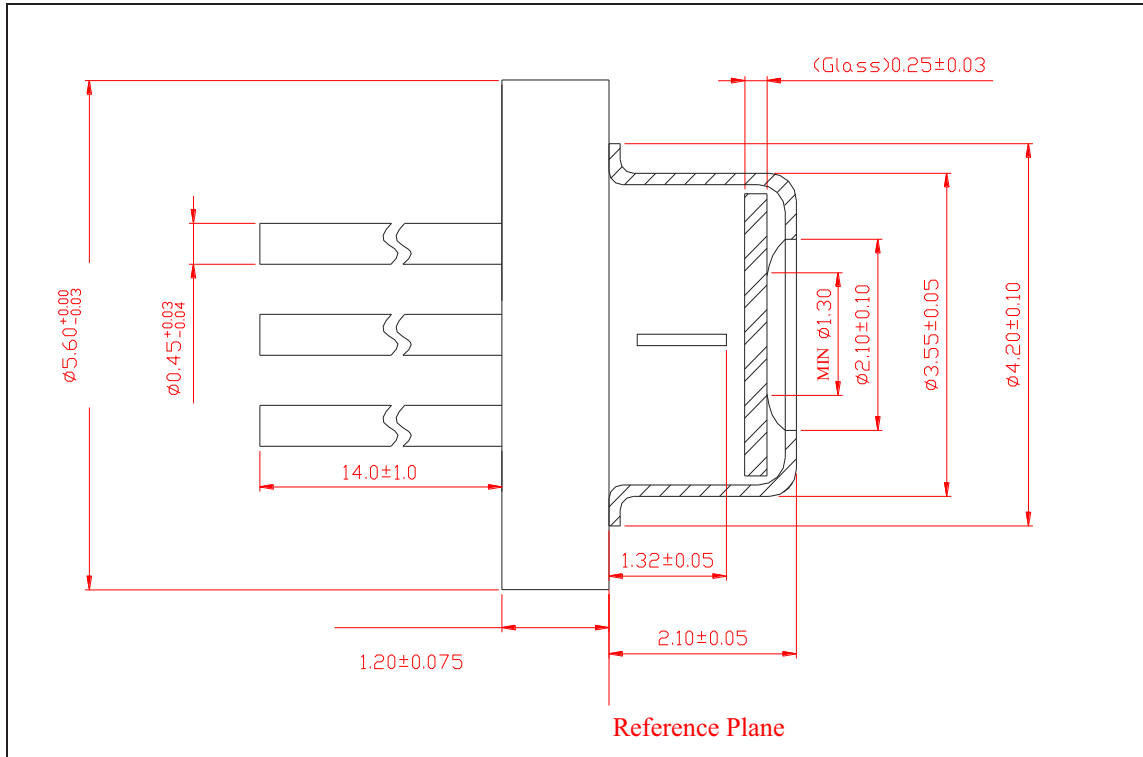
EXS210067-03	
Pin	Function
1	MONITOR DIODE ANODE
2	SLED CATHODE (-), MONITOR DIODE CATHODE , CASE
3	SLED ANODE (+)
4	NC

**SCHEMATIC PIN LAYOUT**



## 6.2 DETAILED DIMENSIONS [mm]

### Side View Cross-section



### Top View

